

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22-2429	SERIAL NO. Filed Herewith		
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U.S. PATENT DOCUMENTS								
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate		
MG	AA	6,175,146 B1	01/16/01	Lane et al.				
MG	AB	6,165,833	12/26/00	Parekh et al.				
MG	AC	6,153,899	11/28/00	Ping				
MG	AD	6,150,211	11/21/00	Zahurak				
MG	AE	6,141,204	10/31/00	Schuegraf et al.				
MG	AF	5,994,749	11/30/99	Oda				
MG	AG	5,972,783	10/26/99	Arni et al.				
MG	AH	5,960,302	09/28/99	Ma et al.				
MG	AI	5,880,989	03/09/99	Wilson et al.				
MG	AJ	5,828,615	10/27/98	Mukunoki et al.				
MG	AK	5,716,864	02/10/98	Abe				
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
MG	AL	WO96/39713	12/12/96	PCT				
	AM							
	AN							
	AO							
	AP							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
MG	AR		C.T. Liu et al., <i>Multiple Gate Oxide Thickness for 2GHz System-on-A-Chip Technologies</i> , 1998 IEEE, pages 21.2.1-21.2.4 (4 pages).					
MG	AS		Lian-Hoon Ko et al., <i>The Effect of Nitrogen Incorporation into the Gate Oxide by Using Shallow Implantation of Nitrogen and Drive-in Process</i> , 1998 IEEE, pages 32-35 (4 pages).					
MG	AT		Brian Doyle et al., <i>Simultaneous Growth of Different Thickness Gate Oxides in Silicon CMOS Processing</i> , 1995 IEEE, pages 301-302 (2 pages).					
EXAMINER Maria Guerrero				DATE CONSIDERED 4-1-04				
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U.S. PATENT DOCUMENTS							
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
MG	AA	5,700,733	12/23/97	Menning			
MG	AB	5,680,344	10/21/97	Seyyed			
MG	AC	5,677,865	10/14/97	Seyyed			
MG	AD	5,674,788	10/07/97	Wristers et al.			
MG	AE	5,638,318	06/10/97	Seyyed			
MG	AF	5,620,908	04/15/97	Inoh et al.			
MG	AG	5,596,218	01/21/97	Soleimani et al.			
MG	AH	5,464,792	11/07/95	Tseng et al.			
MG	AI	5,254,489	10/19/93	Nakata			
MG	AJ	5,880,991	3/1999	Hsu et al.			
	AK						

  

FOREIGN PATENT DOCUMENTS							
Document Number	Date	Country	Class	Subclass	Translation		
					Yes	No	
AL							
AM							
AN							
AO							
AP							

  

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)			
MG	AR	T. Kuroi et al., <i>The Effects of Nitrogen Implantation Into P+ Poly-Silicon Gate On Gate Oxide Properties</i> , 1994 IEEE, pages 107-108	
		(2 pages).	
	AS		
	AT		

  

EXAMINER Maha Guerrero	DATE CONSIDERED 4-1-04
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